

Package	Dim. Fig.	Type	Photo Sensitive Area / mm ²	+/- φ	Characteristics			
					I _{ca} / mA @ E _e / mW/cm ² (V _{CE} = 5 V, λ = 950 nm)	t _r / μs @ R _L / kΩ (I _C = 5 mA, λ = 950 nm)		
Photo Transistors in Hermetically-Sealed Package								
	55	BPW76A	0.36	40°	0.4 to 0.8	1	3.8	0.1
		BPW76B			1.2 (>0.6)			
	56	BPW77NA	0.36	10°	7.5 to 15	1	3.8	0.1
		BPW77NB			20 (>10)			
	57	BPX43	0.76	15°	>0.8	0.5		1
		BPX43-4			2.0 to 4.0		15	
		BPX43-5			3.2 to 6.3		20	
		BPX43-6			>5.0		25	

Photo PIN Diodes

Package	Dim. Fig.	Type	Photo Sensitive Area / mm ²	+/- φ	Characteristics			
					I _{ra} / μA @ λ / nm (E _e = 1 mW/cm ² , V _R = 5 V)	t _{on} / ns @ R _L / Ω (λ = 820 nm, V _R = 10 V)		
Photo PIN Diodes in Clear Plastic Package								
	58	BPW34	7.5	65°	50 (>40)	950	100	1000
	59	BPW46*						
	60	S268P	3 x 7.5	65°				
	48	BPW43	0.25	25°	8 (>4)		4 ¹⁾	50
	61	BPV10	0.78	20°	70 (>30)		2.5 ²⁾	
Photo PIN Diodes with Filter in Plastic Package Matched for GaAlAs IREDs								
	63	BPW82*	7.5	65°	45 (>43)	870	100	1000
	59	BPW83*		60°	85 (>55)			
	65	BPV22NF*			65 (>45)		70	
	65,66	BPV23NF*	5.7					
	62	BPV10NF	0.78	20°	60 (>30)		2.5 ^{1) 2)}	50

1) t_r, t_f 2) V_R = 50 V * long lead packages optional: suffix "L", e.g. BPV23NFL